

# Dielectric and Magnetic Behavior of Polycrystalline Copper Doped Holmium Orthoferrite

Fumiya Tsunawaki, Mitsuhiro Matsuo, Hirokazu Shimooka, and Shigemi Kohiki

*Department of Materials Science, Kyushu Institute of Technology, Kitakyushu 804-8550, Japan*

Polycrystalline  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  sample with  $x = 0, 0.01, 0.05,$  and  $0.1$  exhibited dielectric dispersion at  $350, 225, 115,$  and  $110$  °C with the frequency of  $100$  kHz, respectively. The spin-reorientation temperature of the sample with  $x = 0.1$  was higher by  $2$  K than that with  $x = 0$ . Substitution of Cu for Fe brought about lowering of the dielectric dispersion temperature and rising of the spin-reorientation temperature.

Recent discovery of the ferroelectric state below  $\approx 330$  K of  $\text{LuFe}_2\text{O}_4$  by Ikeda et al.<sup>1</sup> recalled interests in dielectric properties of the rare-earth orthoferrites  $\text{RFeO}_3$  (R: rare-earth element). The  $\text{LuFe}_2\text{O}_4$  demonstrated dielectric dispersion around the magnetic ordering temperature  $\approx 240$  K.<sup>1</sup> The dielectric characteristic temperature of the  $\text{LuFe}_2\text{O}_4$  is rather low for the material utilizable for practical magnetoelectric devices. While there are many studies on the magnetic properties of the  $\text{RFeO}_3$ ,<sup>2,3</sup> there are hardly the reports on dielectric properties. The  $\text{RFeO}_3$  is known to crystallize in an orthorhombically distorted perovskite structure with space group  $Pbnm$ ,<sup>4</sup> and to exhibit weakferromagnetism *WFM* above room temperature *RT*. The  $\text{RFeO}_3$  becomes a promising material with temperature-margins sufficient for practical device applications if it exhibits the dielectric dispersion around the Néel temperature  $T_N$ .  $T_N$  of the holmium orthoferrite  $\text{HoFeO}_3$  is known to be  $\approx 640$  K.<sup>5,6</sup> As a first step to explore a new multifunctional material for practical applications, the dielectric and magnetic behavior of  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  was examined in this study.

In the orthorhombic unit cell of  $\text{RFeO}_3$  the Fe atom is octahedrally coordinated by six oxygen atoms, and the R atoms are located in the large cavities formed by corner-linked  $\text{FeO}_6$  octahedra. One of the oxygen atoms forms the common apex of the two adjacent octahedra, consequently each Fe atom is coupled to six Fe nearest neighbors through the superexchange Fe-O-Fe bond. Since the symmetry of the unit cell is low, the alignment of  $\text{Fe}^{3+}$  spin moments is not strictly antiparallel. Slightly canted  $\text{Fe}^{3+}$  spin moments give rise to a small net magnetization exhibiting *WFM* below  $T_N$ . At *RT* the direction of Fe-sublattice magnetization lies along the *a*-axis, thus a weakferromagnetic moment  $M_{\text{WFM}}$  appears along the *c*-axis. In the field of Fe-sublattice, there is also a contribution due to the paramagnetic susceptibility of the  $\text{R}^{3+}$  ions. At the spin-reorientation temperature  $T_R$  the direction of the net magnetic moment rotates continuously from the *c*-axis to *a*-axis.<sup>7-11</sup> The  $\text{HoFeO}_3$  undergoes spin-reorientation transition at  $\approx 50 - 60$  K.<sup>12,13</sup>

Substitution of Cu for Fe decreases  $M_{\text{WFM}}$  of the  $\text{HoFeO}_3$  because the free ion magnetic moment of  $\text{Cu}^{2+}$  ( $1.9 \mu_B$ ) is smaller

than that of  $\text{Fe}^{3+}$  ( $5.9 \mu_B$ ). Since the Ho-sublattice magnetization remains at a constant, an increase of  $x$  is considered to lower  $T_N$  and to raise  $T_R$  for the  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$ . When the dielectric dispersion occurs around  $T_N$  of the  $\text{HoFeO}_3$ , the  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  is expected to demonstrate lowering of the dielectric dispersion temperature  $T_{\text{disp}}$ , and simultaneously rising of  $T_R$ . Here we report presence of the dielectric dispersion around  $T_N$  of the  $\text{HoFeO}_3$  ( $\approx 365^\circ\text{C}$ ) for the sample with  $x = 0$ , and lowering of  $T_{\text{disp}}$  with  $x$  from  $350^\circ\text{C}$  ( $x = 0$ ) to  $110^\circ\text{C}$  ( $x = 0.1$ ) at the frequency  $f = 100 \text{ kHz}$ , and simultaneous rising of  $T_R$  by 2 K with the increase of  $x$  from 0 to 0.1.

The  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  samples were synthesized by calcination of the mixtures of  $\text{Ho}_2\text{O}_3$ ,  $\alpha\text{-Fe}_2\text{O}_3$  and  $\text{CuO}$  powders. The  $\text{Ho}_2\text{O}_3$  (purity  $>99.9\%$ ),  $\alpha\text{-Fe}_2\text{O}_3$  (purity  $>99.9\%$ ) and  $\text{CuO}$  (purity  $>98\%$ ) reagents were weighed out with the molar ratio of  $\text{Ho} : \text{Fe} : \text{Cu} = 1 : 1-x : x$  ( $x = 0, 0.01, 0.05$ , and  $0.1$ ), and then mixed in grinding. The mixture was heated at  $1000^\circ\text{C}$  for 12 h in flowing oxygen gas. The powders were reground and heated a few times. As shown in the upper panel of Fig. 1, x-ray diffraction peaks for the samples were attributable to the orthorhombic perovskite structure. The lattice constants of the sample with  $x = 0$  ( $a = 5.282$ ,  $b = 5.592$  and  $c = 7.607 \text{ \AA}$ ) were in agreement with those reported ( $a = 5.282$ ,  $b = 5.592$  and  $c = 7.608 \text{ \AA}$ ).<sup>14</sup> As shown by the lower panel of Fig. 1, the lattice constants of the orthorhombic unit cell, especially those along the  $a$ - and  $c$ -axes, increased with  $x$ . Such increase of the lattice constants is expected to accompany with an elongation of the superexchange Fe-O-Fe bond, and then to lessen the cant angle  $\theta$  of the Fe-sublattice magnetization relative to the  $a$ -axis. Judging from the ionic radii of  $\text{Fe}^{3+}$  ( $0.65 \text{ \AA}$ ),  $\text{Cu}^{2+}$  ( $0.73 \text{ \AA}$ ) and  $\text{Ho}^{3+}$  ( $0.90 \text{ \AA}$ ), the  $\text{Cu}^{2+}$  substituted for the  $\text{Fe}^{3+}$  of the  $\text{HoFeO}_3$  lattice. Smaller  $\theta$  and/or smaller  $M_{\text{WFM}}$  by the substitution would give rise to

lowering of  $T_N$  and rising of  $T_R$ .

As shown in Fig. 2, all the samples exhibited characteristic frequency dispersion in temperature dependence of the dielectric constant  $\epsilon'$ . It is known that such dielectric relaxation phenomena are resulted from nano-scale polar-regions presented in the order-disorder type of ferroelectric materials, where motion of the ferroelectric domain boundary gives rise to the dispersion. The substitution is considered to bring about disorder in the arrangement of ion valence on the crystallographically equivalent Fe sites. The electric polarization with mesoscopic order in the  $\text{HoFeO}_3$  was affected by statistical compositional fluctuation. The sample with  $x = 0$  exhibited the dielectric dispersion around  $T_N$  ( $\approx 365^\circ\text{C}$ ) of  $\text{HoFeO}_3$ .  $T_{\text{disp}}$  at  $f = 100 \text{ kHz}$  of the samples with  $x = 0, 0.01, 0.05$ , and  $0.1$  were  $350, 225, 115$ , and  $110^\circ\text{C}$ , respectively. An increase of  $x$  lowered  $T_{\text{disp}}$  rather rapidly, but  $\epsilon'$  decreased linearly from 45 ( $x = 0$ ) to 24 ( $x = 0.1$ ). The Debye curves for dielectric dispersion  $\epsilon'$  and absorption  $\epsilon''$  are symmetric about  $\omega\tau = 1$ . The midpoint of  $\epsilon'$  curve and the maximum of  $\epsilon''$  curve occur at a frequency of  $\omega_{\text{max}} = 1/\tau$ . At a given temperature  $T_p$ , such a characteristic response frequency was found at a peak in the frequency variation of  $\epsilon'$ . The value of the relative variation of  $T_p$  per decade of  $f$ ,  $(\Delta T_p/T_p)/\Delta(\log_{10}f)$ , for the samples with  $x = 0, 0.01, 0.05$  and  $0.1$  were  $0.37, 0.22, 0.38$ , and  $0.34$ , respectively. They place the samples in the range of non-interacting fine particles.<sup>15</sup> It is well known that the frequency dependence of  $T_p$  obeys an Arrhenius relation:  $f = f_0 \exp(-E_a/k_B T)$  where  $f$  is the measured frequency,  $k_B T$  is the thermal energy,  $f_0$  is a prefactor usually thought of as an attempt frequency, and  $E_a$  is the activation energy for polarization fluctuation of each polar-region. When we assume  $f_0 = 3 \times 10^{11} \text{ Hz}$ , the values of  $E_a$  for the samples with  $x = 0, 0.01, 0.05$  and  $0.1$

are estimated to 0.95, 0.73, 0.57, and 0.55 eV, respectively.  $E_a$  decreased rather rapidly with  $x$ , as well as  $T_{\text{disp}}$ .

Field dependent magnetization of the samples with  $x = 0$  and 0.1 measured at 300 K are shown in the upper panel of Fig. 3. The sample with  $x = 0$  demonstrated a sharp increase of magnetization with increasing the applied field  $H$  below  $H = 0.05$  T, and a linear field dependence of magnetization above  $H = 0.05$  T. The sample with  $x = 0.1$  showed only the linear field dependence of magnetization. Such field dependences of magnetization were resulted from *WFM* based on the superexchange Fe-O-Fe bond. Extrapolation of a line fitted to the linear portion of the  $M$ - $H$  curve intersects at a point of  $M = M_{\text{WFM}}$  and of  $H = H_i$ .  $H_i$  is the internal field acting on the Ho sites.<sup>16</sup>  $M_{\text{WFM}}$  and  $H_i$  amounted to  $\approx 0.01 \mu_B/\text{Fe}$  and  $\approx -0.1$  T, respectively.  $H_i$  is antiparallel to  $H$ . An enhancement of the antiferromagnetic coupling for the sample with  $x = 0.1$  is apparent, as shown in the lower panel of Fig. 3. The sample with  $x = 0$  indicated *WFM* above  $\approx 180$  K, antiferromagnetism at  $\approx 180$ -70 K with the Weiss temperature  $\Theta \approx -100$  K, spin-reorientation at  $\approx 70$ -50 K, and paramagnetism below  $\approx 50$  K. A possible origin of the change at  $\approx 180$  K is crossover of the anisotropy contribution. The sample with  $x = 0.1$  demonstrated antiferromagnetic behavior at the temperature ranging from  $\approx 300$  K to  $\approx 70$  K with  $\Theta \approx -300$  K. Remarkable decrease of  $M_{\text{WFM}}$  by the substitution is also indicated by the inset. The enlarged zero-field-cooled (*ZFC*) magnetization around  $T_R$  showed the peak-top shift of +2 K by the substitution. This is considered to be due to the smaller magnetic moment of the  $\text{Cu}^{2+}$  and/or a decrease of  $\theta$  for antiferromagnetically coupled spin moments. Such  $T_R$  shift by the substitution was reconfirmed by employing the thermoremanence *TMR* which determines the phase transition temperatures of polycrystalline samples.<sup>17</sup> Considerable

difference between the field-cooled (*FC*) and *ZFC* magnetization appeared below 70 K (not shown). The temperature of the *TMR* curve falls down to a background level were 60 K and 63 K for the sample with  $x = 0$  and 0.1, respectively. The substitution raised  $T_R$  as it was expected.

The  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  samples were highly resistive at 300 K. The order of the *ac* resistivity stayed at  $10^6 \Omega\text{cm}$  at  $f = 100$  kHz even when  $\text{Cu}^{2+}$  substituted for  $\text{Fe}^{3+}$ . The upper panel of Fig. 4 shows an enlargement of the optical absorption ranging from 1.5 to 2 eV with  $x$ . As shown by the difference spectra in Fig. 4, especially the absorption peaked at 1.5 eV grew rapidly with  $x$ . In the octahedral crystal field, the five-fold-degenerated  $3d$ -orbital splits into three-fold  $t_{2g}$  and two-fold  $e_g$  orbitals. These states line up  $t_{2g\uparrow}$ ,  $e_{g\uparrow}$ ,  $t_{2g\downarrow}$ , and  $e_{g\downarrow}$  with increasing the energy, where  $\uparrow$  and  $\downarrow$  represent the up-spin and down-spin states, respectively. The electronic configuration for  $\text{Fe}^{3+}$  in the high-spin state is  $t_{2g\uparrow}^3$  and  $e_{g\uparrow}^2$ , and that for  $\text{Cu}^{2+}$  is  $t_{2g\uparrow}^3$ ,  $e_{g\uparrow}^2$ ,  $t_{2g\downarrow}^1$ , and  $e_{g\downarrow}^1$ . Since the  $e_{g\downarrow}^1$  state of  $\text{Cu}^{2+}$  is half-filled, the Fermi level of the Cu substituted samples are considered to align at the middle of the fundamental band gap (the energy difference between the  $e_{g\uparrow}^2$  and  $t_{2g\downarrow}$  states) of the sample with  $x = 0$ . As illustrated in the lower panel of Fig. 4, electron transition between the  $\text{Cu}^{2+}$   $e_{g\downarrow}^1$  state and the  $\text{Fe}^{3+}$   $t_{2g\downarrow}$  empty state brings about the optical absorption at the energy below the fundamental absorption energy. Because all the samples are fundamentally highly resistive, electron hopping between the  $\text{Cu}^{2+}$   $e_{g\downarrow}^1$  state and the  $\text{Fe}^{3+}$   $t_{2g\downarrow}$  empty state cannot be expected for the  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  samples even when the electron transition corresponds to the experimentally observed absorption peaked at 1.5 eV. The partially filled  $e_g$  band is expected to play a key role in the electronic properties of  $3d$ -transition metal oxides. The  $\text{Cu}^{2+}$  substitution for  $\text{Fe}^{3+}$  would also give rise to generation of  $\text{Fe}^{4+}$

with  $t^3_{2g\uparrow}$  and  $e^1_{g\uparrow}$  to preserve the charge neutrality for the  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$ . Since the full-filled  $e^2_{g\uparrow}$  state of  $\text{Fe}^{3+}$  and the half-filled  $e^1_{g\uparrow}$  state of  $\text{Fe}^{4+}$  are considered to locate at the same energy level, electron hopping between  $\text{Fe}^{3+}$  and  $\text{Fe}^{4+}$  would partially occur in the  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  samples.

The  $\text{HoFe}_{1-x}\text{Cu}_x\text{O}_3$  samples exhibited the dielectric dispersion indicating a typical character of order–disorder type ferroelectric materials.  $T_{\text{disp}}$  of the sample with  $x = 0$  was  $\approx 350^\circ\text{C}$  at  $f = 100$  kHz. The substitution of

Cu for Fe lowered  $T_{\text{disp}}$  from  $350^\circ\text{C}$  ( $x = 0$ ) to  $110^\circ\text{C}$  ( $x = 0.1$ ). The increase of  $x$  from 0 to 0.1 raised simultaneously  $T_{\text{R}}$  by 2 K. The valence fluctuation in the Fe-sublattice played a central role for the dielectric response of  $\text{HoFeO}_3$ .

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Fig. 1 by K.O/ KIT, JPN

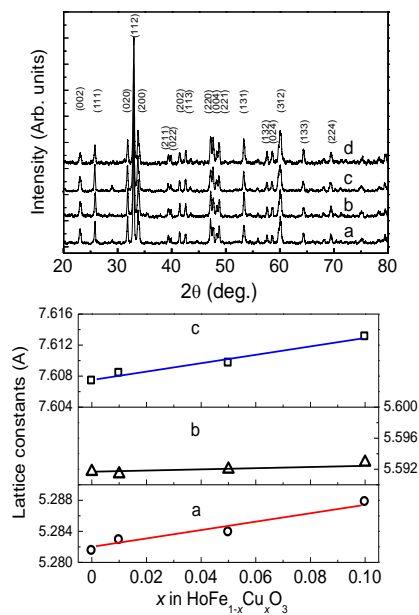


Fig. 1 X-ray diffraction patterns (upper panel) and lattice constants for the orthorhombic unit cell (lower panel) of the samples with  $x = 0$  (a), 0.01 (b), 0.05 (c), and 0.1 (d) measured with a Rigaku CN2013 diffractometer with Cu  $K\alpha$  radiation.

Fig. 2 by K.O/ KIT, JPN

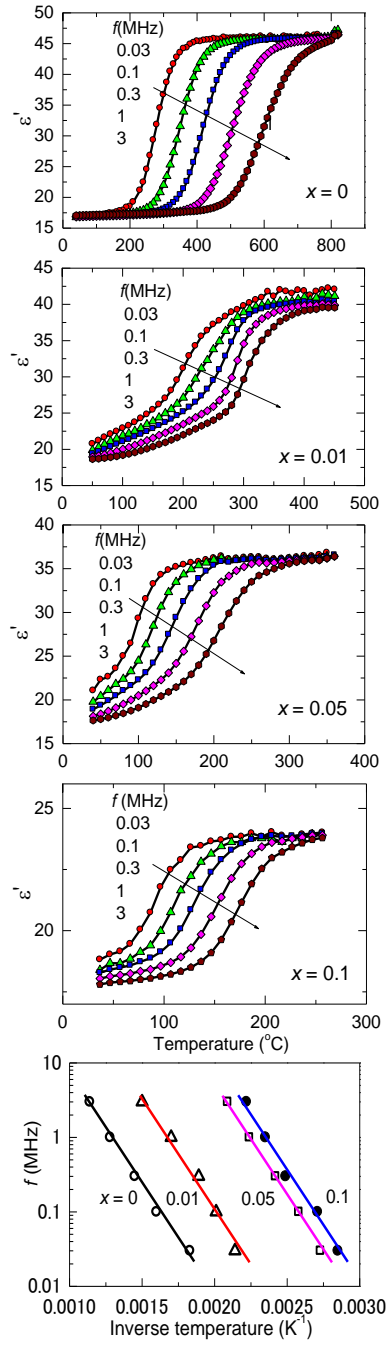


Fig. 2 Dielectric dispersion and temperature variation of the characteristic frequency of the samples with  $x = 0, 0.01, 0.05,$  and  $0.1$  measured with a HP 4291 RF impedance analyzer. The dielectric constant measured at the frequency ranging from 30 kHz to 3 MHz in the external field  $E = 245$  V/cm. The Arrhenius relation is indicated by a solid line for each sample.

Fig. 3 by K.O/ KIT, JPN

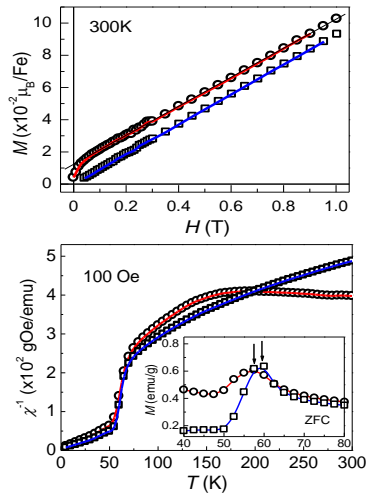


Fig. 3 Initial magnetization curves (upper panel) and temperature dependence of inverse susceptibility (lower panel) of the samples with  $x = 0$  ( $\circ$ ) and  $0.1$  ( $\square$ ) measured at 300 K by a Quantum Design MPMS 5S SQUID magnetometer. Inset: enlarged magnetization curves around  $T_R$  of the samples cooled in the field of 100 Oe. The arrows indicate the top of the curves.

Fig. 4 by K.O/ KIT, JPN

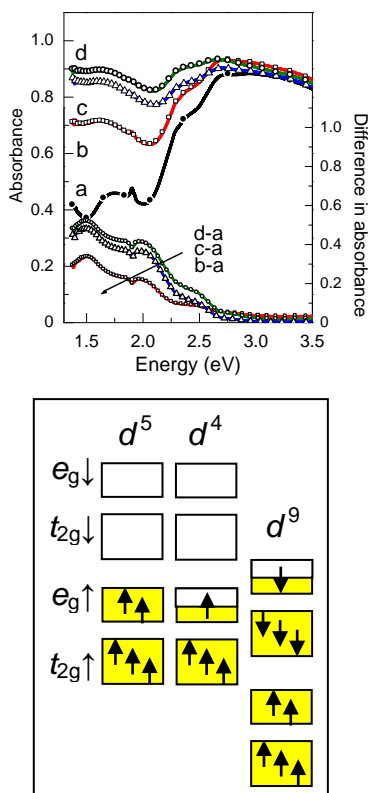


Fig. 4 Upper panel: ultraviolet-visible absorption spectra (the left hand side scale) of the samples with  $x = 0$  (a), 0.01 (b), 0.05 (c), and 0.1 (d) measured with a JASCO V-550 spectrometer. Difference spectra (the right hand side scale) between the samples  $x = 0.01$  and 0 (b – a),  $x = 0.05$  and 0 (c – a), and  $x = 0.1$  and 0 (d – a), are also presented. Lower panel: scheme of the electronic states of  $\text{Fe}^{3+}$  ( $d^5$ ),  $\text{Fe}^{4+}$  ( $d^4$ ) and  $\text{Cu}^{2+}$  ( $d^9$ ) in the octahedral crystal field.